

C2 ~~113/~~ (Amended) An EL display device comprising:

at least one thin film transistor formed over a substrate;

a first insulating layer comprising silicon nitride formed over said thin film transistor;

a second insulating layer comprising organic resin formed over said first insulating

layer;

a third insulating layer comprising DLC formed over said second insulating layer;

a pixel electrode formed over said third insulating layer, said pixel electrode electrically connected to said thin film transistor; and

a light-emitting layer formed over said third insulating layer.

C3 ~~115/~~ (Amended) An EL display device according to claim 113, wherein said second insulating layer has a planarized surface.

C4 ~~117/~~ (Amended) An EL display device comprising:

at least one thin film transistor formed over a substrate;

a first insulating layer comprising organic resin formed over said thin film transistor;

a second insulating layer comprising DLC formed over said first insulating layer;

a third insulating layer comprising organic resin formed over said second insulating

layer;

a pixel electrode formed over said third insulating layer, said pixel electrode electrically connected to said thin film transistor; and

a light-emitting layer formed over said third insulating layer.

C6 ~~121/~~ (Amended) An EL display device comprising:

an active matrix region and a driver region formed over a substrate,

wherein said active matrix region comprises:

at least one thin film transistor;

a first insulating layer comprising organic resin formed over said thin film transistor;

a second insulating layer comprising DLC formed over said first insulating layer;

a pixel electrode formed over said second insulating layer, said pixel electrode electrically connected to said thin film transistor; and

a light-emitting layer formed over said second insulating layer.

125. (Amended) An EL display device comprising:

an active matrix region and a driver region over a substrate,

wherein said active matrix region comprises:

at least one thin film transistor;

a first insulating layer comprising silicon nitride formed over said thin film transistor;

a second insulating layer comprising organic resin formed over said first insulating

layer;

a third insulating layer comprising DLC formed over said second insulating layer;

a pixel electrode formed over said third insulating layer, said pixel electrode electrically connected to said thin film transistor; and

a light-emitting layer formed over said third insulating layer.

127. (Amended) An EL display device according to claim 125, wherein said second insulating layer has a planarized surface.

129. (Amended) An EL display device comprising:

an active matrix region and a driver region over a substrate,

wherein said active matrix region comprises:

at least one thin film transistor;